

HIGH-FREQUENCY DEVICE

Abstract

A high-frequency device has a semiconductor substrate; a high-frequency circuit layer formed on the substrate and including a circuit element and a multilayer wiring layer; electrically conductive pads; rewiring layers connected to the electrically conductive pads; an electrically insulating sealing layer formed on the first electrically insulating layer and the rewiring layer and having a thickness larger than the multilayer wiring layer; electrically conductive posts provided inside the electrically insulating sealing layer and between the rewiring layer and the mounting connection terminals. A first electrically conductive post corresponding to a power source has a first diameter; a second electrically conductive post corresponding to an input of input amplifier has a second diameter less than the first diameter; and a third electrically conductive post corresponding to an output of power output amplifier has a third diameter larger than the second diameter.